

*In the claims:*

1-21. (Cancelled)

22. (Previously presented) A method of forming an electronic apparatus, comprising:

providing a flexible substrate;

providing a single crystalline silicon substrate disposed adjacent to the flexible substrate, wherein the flexible substrate is bonded to the single crystalline substrate by an ion implantation process through the flexible substrate to an interface of the flexible substrate and the single crystalline silicon substrate; and

providing a plurality of semiconductor devices formed on the single crystalline silicon substrate.

23. (Original) The method of claim 22, wherein the electronic apparatus is a flexible flat panel display.

24. (Original) The method of claim 22, wherein the electronic apparatus is a flexible printed circuit board.

25. (Original) The method of claim 22, wherein the ion implantation process uses a noble gas.

26. (Original) The method of claim 22, wherein the ion implantation process uses a gas selected from the group consisting of hydrogen, helium, xenon, and krypton.

27. (Original) The method of claim 22, wherein the flexible substrate includes a polymer material.

28. (Original) The method of claim 22, wherein the flexible substrate includes a material selected from the group consisting of polymer, plastic, paper, flexible glass, and stainless steel.

29. (Original) The method of claim 22, wherein the plurality of semiconductor devices includes thin film transistors.